NSN 5961-01-132-8730

Transistor - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5961-01-132-8730

Inclosure Material:
Metal
Overall Length:
1.252 inches
Overall Height:
0.340 inches
Overall Width:
0.700 inches
End Application:
Flight set 76301
Mounting Facility Quantity:
2
Internal Configuration:
Junction contact
Joint Electronic Device Engineering Council/jedec/case Outline Designation:
To-66
Electrode Internally-electrically Connected To Case:
Collector
Mounting Method:
Unthreaded hole
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
6.0 emitter to base voltage, static, collector open and 250.0 collector to base voltage/static/emitter open and 200.0 collector to emitter
voltage/static/base open
Current Rating Per Characteristic:
2.00 amperes source cutoff current and 0.50 amperes source cutoff current
Power Rating Per Characteristic:
20.0 watts small-signal input power, common-collector preset
Maximum Operating Tempurature Per Measurement Point:
200.0 degrees celsius junction
Special Features:
Junction pattern arrangement: npn
Precious Material And Location:
Terminal surface option gold
Precious Material:
Gold
Test Data Document:
81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification
format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

91240 mil a 10500/454 government appoification

Terminal Type And Quantity:
1 case and 2 uninsulated wire lead

Specification Data:

NSN 5961-01-132-8730

Transistor - Page 2 of 2



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J	116		_	HG.

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

A110a0